

## CLAIMS

### What is claimed is:

1. An electrode structure for a display device having at least one emitter, comprising:  
a first electrode located adjacent said at least one emitter;  
a second electrode; and  
an insulating layer disposed between the first electrode and the second electrode including a ridge  
located closer to said at least one emitter than a portion of first electrode or a portion of  
the second electrode.
2. The electrode structure of claim 1, wherein the second electrode comprises a layer  
of conductive material disposed on a plane over the insulating layer, and the first electrode  
comprises a layer of conductive material disposed on a plane under the insulating layer.
3. The electrode structure of claim 2, wherein the first electrode is a gate electrode  
and the second electrode is a focusing electrode.
4. The electrode structure of claim 3, wherein the insulating layer comprises silicon  
oxide.
5. The electrode structure of claim 1, wherein a second insulating layer is disposed  
between the insulating layer and the first electrode.
6. The electrode structure of claim 5, wherein the second insulating layer comprises  
silicon nitride.
7. The electrode structure of claim 1, wherein the first electrode comprises a first  
layer of conductive material and the second electrode comprises a second layer of conductive  
material, the first and second layers of conductive material being disposed on a single plane  
above the emitter.

8. The electrode structure of claim 7, wherein the insulating layer further comprises a ridge protruding above an upper surface of the first electrode or the second electrode.

9. The electrode structure of claim 8, wherein the insulating layer comprises silicon oxide.

10. The electrode structure of claim 1, wherein at least one of the first electrode and the second electrode comprises polysilicon, titanium, aluminum, or tungsten.

11. The electrode structure of claim 2, further comprising:  
at least one additional insulation layer disposed on a plane over the second electrode; and  
at least one additional electrode comprising a layer of conductive material disposed on a plane over the at least one additional insulation layer.

12. The electrode structure of claim 7, further comprising:  
at least one additional electrode comprising a layer of conductive material disposed on the single plane above the emitter; and  
at least one additional insulating layer disposed between the second electrode and the at least one additional electrode.

13. A display device, comprising an electrode structure having:  
a gate electrode located adjacent an emitter;  
a focusing electrode; and  
an insulating layer disposed between the gate electrode and the focusing electrode including a ridge protruding closer to the emitter than one of a sidewall of the gate electrode and a sidewall of the focusing electrode.

14. The device of claim 13, wherein the focusing electrode comprises a layer of conductive material disposed on a plane over the insulating layer, and the gate electrode comprises a layer of conductive material disposed on a plane under the insulating layer.
15. The device of claim 14, wherein the insulating layer comprises silicon oxide.
16. The device of claim 15, wherein a second insulating layer is disposed between the insulating layer and the gate electrode.
17. The device of claim 16, wherein the second insulating layer comprises silicon nitride.
18. The device of claim 13, wherein the gate electrode comprises a first layer of conductive material and the focusing electrode comprises second a layer of conductive material, the first and second layers of conductive material being disposed on a single plane above the emitter.
19. The device of claim 18, wherein the insulating layer further comprises a ridge protruding above an upper surface of the gate electrode or the focusing electrode.
20. The device of claim 19, wherein the insulating layer comprises silicon oxide.
21. The device of claim 13, wherein at least one of the gate electrode and the focusing electrode comprises polysilicon, titanium, aluminum, or tungsten.
22. The device of claim 14, further comprising:  
at least one additional insulation layer disposed on a plane over the focusing electrode; and  
at least one additional electrode comprising a layer of conductive material disposed on a plane over the at least one additional insulation layer.

23. The device of claim 18, further comprising:  
at least one additional electrode comprising a layer of conductive material disposed on the single  
plane above the emitter; and  
at least one additional insulating layer disposed between the focusing electrode and the at least  
one additional electrode.